TOSHIBA Transistor Silicon PNP Epitaxial Type

# 2SB1495

### **High-Power Switching Applications**

- High DC current gain:  $h_{FE} = 2000$  (min) ( $V_{CE} = -2$  V,  $I_{C} = -2$  A)
- Low saturation voltage:  $V_{CE (sat)} = -1.5 \text{ V (max) (IC} = -1.5 \text{ A)}$
- Complementary to 2SD2257

### **Absolute Maximum Ratings (Tc = 25°C)**

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V <sub>CBO</sub>	-100	$(\nearrow)$
Collector-emitter voltage		V <sub>CEO</sub>	-100	$\langle \langle u \rangle \rangle$
Emitter-base voltage		V <sub>EBO</sub>	-8	V
Collector current	DC	IC	-3	> A
	Pulsed	I <sub>CP</sub>	-5	V 7
Base current		ΙΒ	-0.3	Α
Collector power dissipation	Ta = 25°C	P <sub>C</sub>	2.0	W
	Tc = 25°C	FC (	20	< <b>~</b>
Junction temperature		T <sub>j</sub> ((	150	°C/
Storage temperature range		T <sub>stg</sub>		°C \

Unit: mm

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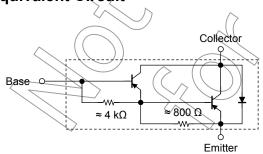
Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

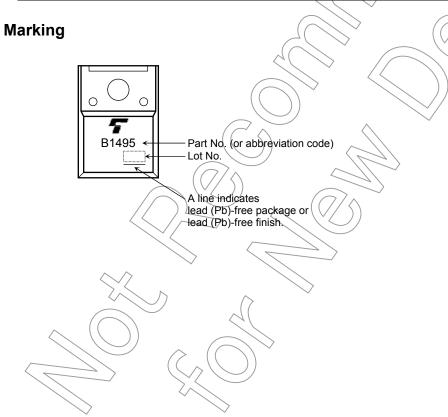
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Equivalent Circuit

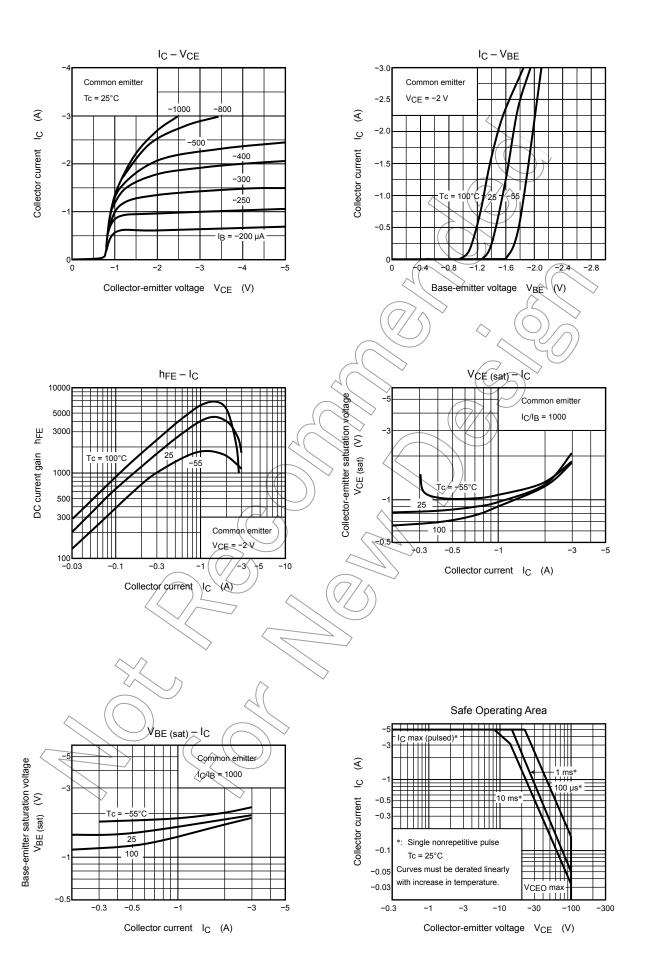


# Electrical Characteristics (Tc = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I <sub>CBO</sub>	V <sub>CB</sub> = -100 V, I <sub>E</sub> = 0	_	_	-10	μΑ
Emitter cut-off cu	rrent	I <sub>EBO</sub>	V <sub>EB</sub> = -8 V, I <sub>C</sub> = 0	-0.8	_	-4.0	mA
Collector-emitter	breakdown voltage	V (BR) CEO	I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0	-100	_	_	V
DC current gain		h <sub>FE (1)</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -1 A	2000	_	_	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -2 A	2000	) /-	_	
Collector-emitter	saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = -1.5 A, I <sub>B</sub> = -1.5 mA	$\nearrow$	_	-1.5	V
Base-emitter saturation voltage		V <sub>BE</sub> (sat)	I <sub>C</sub> = -1.5 A, I <sub>B</sub> = -1.5 mA	))	_	-2.0	V
Switching time	Turn-on time	t <sub>on</sub>	20 μs Input Output	· _	0.5	_	
	Storage time	t <sub>stg</sub>		- (	1.0		μs
	Fall time	t <sub>f</sub>	$V_{CC} \approx -30$ $V_{$		0.4	_	



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